# Reliability Testing Summary
# 0.22 µm

**Technology:** Si Gate CMOS
**Device Type:** XCVXXX
**Package Type:** Various
**Assumed Activation Energy:** 0.70 ev @ C.L. = 60%

| | Life Test | Hast | Temp. Cycle |
|---|---|---|---|
| | 145C | 100 Hrs 130C/85% | 1,000Cycs. -65C/+150C |
| Combined Lot: | 21 | 1 | 1 |
| Failures: | 6 | 0 | 0 |
| Device on test: | 1,025 | 23 | 34 |
| Actual device hours: | 1,117,744 | 2,300 | 34,000 |
| Mean: | 1,090 | 100 | 1,000 |
| Equivalent device hours @ Tj=125C: | 2,967,035 | | |
| Equivalent device hours @ Tj=70C: | 230,903,313 | | |
| Equivalent device hours @ Tj=25C: | 2.79E+09 | | |
| Failure Rate in FITS @ Tj=70C: | 32 | | |
| Failure Rate in FITS @ Tj=25C: | 3 | | |

*The data collected from process qualification & Reliability monitor program

# Reliability Testing Summary
# 0.18 µm

| | |
|---|---|
| Technology: | Si Gate CMOS |
| Device Type: | XCVXXXE |
| Package Type: | Various |
| Assumed Activation Energy: | 0.70 ev @ C.L. = 60% |

| | Life Test | Hast | Temp. Cycle |
|---|---|---|---|
| | 145C | 100Hrs 130C/85% | 1,000Cycs. -65C/+150C |
| Combined Lot: | 13 | 1 | 1 |
| Failures: | 2 | 0 | 0 |
| Device on test: | 500 | 76 | 68 |
| Actual device hours: | 318,156 | 7,600 | 68,000 |
| Mean: | 636 | 100 | 1,000 |
| Equivalent device hours @ Tj=125C: | 844,540 | | |
| Equivalent device hours @ Tj=70C: | 65,724,597 | | |
| Equivalent device hours @ Tj=25C: | 7.95E+08 | | |
| Failure Rate in FITS @ Tj=70C: | 47 | | |
| Failure Rate in FITS @ Tj=25C: | 4 | | |

*The data collected from process qualification & Reliability monitor program